



**PATENT APPLICATION**

**RESPONSE UNDER 37 CFR §1.116  
EXPEDITED PROCEDURE  
TECHNOLOGY CENTER ART UNIT 2813**

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Teruo Takizawa et al.

Group Art Unit: 2813

Application No.: 09/763,365

Examiner: D. Hogans

Filed: February 23, 2001

Docket No.: 108680

For: SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF

**AMENDMENT AFTER FINAL REJECTION UNDER 37 CFR §1.116**

Director of the U.S. Patent and Trademark Office  
Washington, D.C. 20231

Sir:

In reply to the September 26, 2002 Office Action, the period for response being extended by the attached Petition for Extension of Time, please amend the above identified application as follows:

**IN THE CLAIMS:**

Please cancel claim 3 without prejudice or disclaimer.

Please replace claims 1 and 7 as follows:

1. (Twice Amended) A semiconductor device, comprising:

a metal-oxide-semiconductor field-effect transistor that includes:

a gate insulation film and a gate electrode on the gate insulation film,  
the gate electrode including a germanium film on the gate insulation film, wherein p-type impurities are doped into said germanium film.

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